

FDD8426H-VB Datasheet

N- and P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
N-Channel	30	0.007 at V _{GS} = 10 V	65	6 nC
		0.010 at V _{GS} = 4.5 V	50	
P-Channel	- 30	0.025 at V _{GS} = - 10 V	- 35	8 nC
		0.035 at V _{GS} = - 4.5 V	- 25	

FEATURES

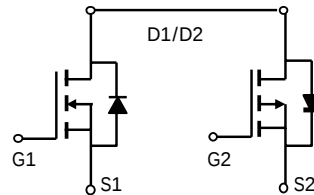
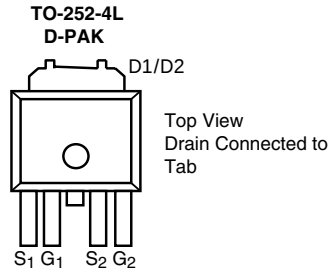
- Halogen-free According to IEC 61249-2-21 Available
- Trench Power MOSFET
- 100 % R_g and UIS Tested

APPLICATIONS

- CCFL Inverter



RoHS
COMPLIANT
HALOGEN
FREE
Available



N-channel

P-channel

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V _{DS}	30	- 30	V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	65	- 35	A
	T _C = 70 °C		45	- 25	
	T _A = 25 °C		20 ^{b, c}	- 17 ^{b, c}	
	T _A = 70 °C		14 ^{b, c}	- 12 ^{b, c}	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	195	- 95	
Source Drain Current Diode Current	T _C = 25 °C	I _S	2.6	- 2.8	
	T _A = 25 °C		1.7 ^{b, c}	- 1.7 ^{b, c}	
Pulsed Source-Drain Current		I _{SM}	20	- 15	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	20	15	mJ
Single Pulse Avalanche Energy		E _{AS}	8.1	13	
Maximum Power Dissipation	T _C = 25 °C	P _D	9.1	8.4	W
	T _C = 70 °C		6	5	
	T _A = 25 °C		2 ^{b, c}	2 ^{b, c}	
	T _A = 70 °C		1.3 ^{b, c}	1.3 ^{b, c}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	N-Channel		P-Channel		Unit
			Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	55	62.5	53	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	33	40	30	37	

Notes:

a. Based on T_C = 25 °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. Maximum under Steady State conditions is 110 °C/W for N-Channel and P-Channel.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit	
Static								
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	N-Ch	30			V	
		V _{GS} = 0 V, I _D = - 250 μA	P-Ch	- 30				
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA	N-Ch		55		mV	
		I _D = - 250 μA	P-Ch		- 50			
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J	I _D = 250 μA	N-Ch		- 6			
		I _D = - 250 μA	P-Ch		4			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	1		3	V	
		V _{DS} = V _{GS} , I _D = - 250 μA	P-Ch	- 1		- 3		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	N-Ch P-Ch			100 - 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	N-Ch			1	μA	
		V _{DS} = - 30 V, V _{GS} = 0 V	P-Ch			- 1		
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	N-Ch			10		
		V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C	P-Ch			- 10		
On-State Drain Current ^b	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	N-Ch	20			A	
		V _{DS} ≤ - 5 V, V _{GS} = - 10 V	P-Ch	- 25				
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 7 A	N-Ch		0.007		Ω	
		V _{GS} = - 10 V, I _D = - 6 A	P-Ch		0.025			
		V _{GS} = 4.5 V, I _D = 6 A	N-Ch		0.010			
		V _{GS} = - 4.5 V, I _D = - 5 A	P-Ch		0.035			
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 7 A	N-Ch		15		S	
		V _{DS} = - 15 V, I _D = - 6 A	P-Ch		8.5			
Dynamic ^a								
Input Capacitance	C _{iss}	N-Channel V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	N-Ch P-Ch		625 950		pF	
Output Capacitance	C _{oss}		N-Ch P-Ch		65 85			
Reverse Transfer Capacitance	C _{rss}	P-Channel V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz	N-Ch P-Ch		40 60			
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 4.3 A	N-Ch		13	20	nC	
		V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 3.1 A	P-Ch		14.5	22		
Gate-Source Charge	Q _{gs}	N-Channel V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 4.3 A	N-Ch P-Ch		6 8	9 12		
			N-Ch P-Ch		2.3 2.2			
Gate-Drain Charge	Q _{gd}	P-Channel V _{DS} = - 15 V, V _{GS} = - 4.5 V, I _D = - 3.1 A	N-Ch P-Ch		2.6 3.7			
Gate Resistance	R _g	f = 1 MHz	N-Ch P-Ch		2 14	3 20		Ω

SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit	
Dynamic ^a								
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 30 V, R _L = 8.8 Ω I _D ≅ 3.4 A, V _{GEN} = 4.5 V, R _g = 1 Ω	N-Ch		15	25	ns	
			P-Ch		30	45		
Rise Time	t _r		N-Ch		65	100		
			P-Ch		70	105		
Turn-Off Delay Time	t _{d(off)}	P-Channel V _{DD} = - 30 V, R _L = 12.5 Ω I _D ≅ - 2.4 A, V _{GEN} = - 4.5 V, R _g = 1 Ω	N-Ch		15	25		
			P-Ch		40	60		
Fall Time	t _f		N-Ch		10	15		
			P-Ch		30	45		
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 30 V, R _L = 8.8 Ω I _D ≅ 3.4 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch		10	15		
			P-Ch		10	15		
Rise Time	t _r		N-Ch		15	25		
			P-Ch		13	20		
Turn-Off Delay Time	t _{d(off)}	P-Channel V _{DD} = - 30 V, R _L = 12.5 Ω I _D ≅ - 2.4 A, V _{GEN} = - 10 V, R _g = 1 Ω	N-Ch		20	30		
			P-Ch		35	55		
Fall Time	t _f		N-Ch		10	15		
			P-Ch		30	45		
Drain-Source Body Diode Characteristics								
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	N-Ch			2.6	A	
			P-Ch			- 2.8		
Pulse Diode Forward Current ^a	I _{SM}		N-Ch			20		
			P-Ch			- 25		
Body Diode Voltage	V _{SD}	I _S = 1.7 A	N-Ch		0.8	1.2	V	
		I _S = - 2 A	P-Ch		- 0.8	- 1.2		
Body Diode Reverse Recovery Time	t _{rr}	N-Channel I _F = 1.7 A, dI/dt = 100 A/μs, T _J = 25 °C	N-Ch		30	60	ns	
			P-Ch		30	50		
Body Diode Reverse Recovery Charge	Q _{rr}		P-Channel I _F = - 2 A, dI/dt = - 100 A/μs, T _J = 25 °C	N-Ch		32	50	nC
				P-Ch		35	60	
Reverse Recovery Fall Time	t _a			N-Ch		25		ns
				P-Ch		16		
Reverse Recovery Rise Time	t _b		N-Ch		5			
			P-Ch		14			

Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

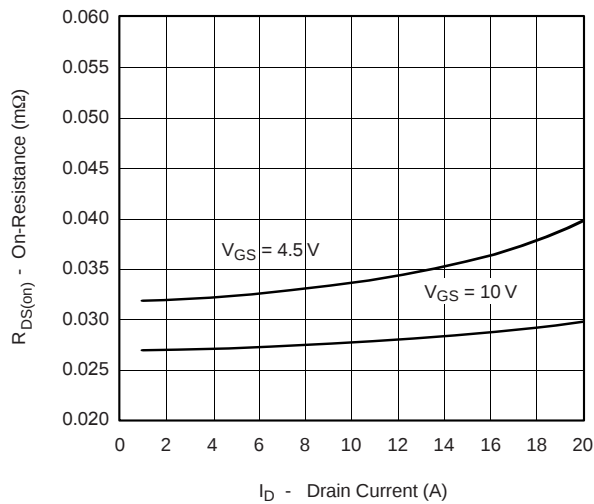
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



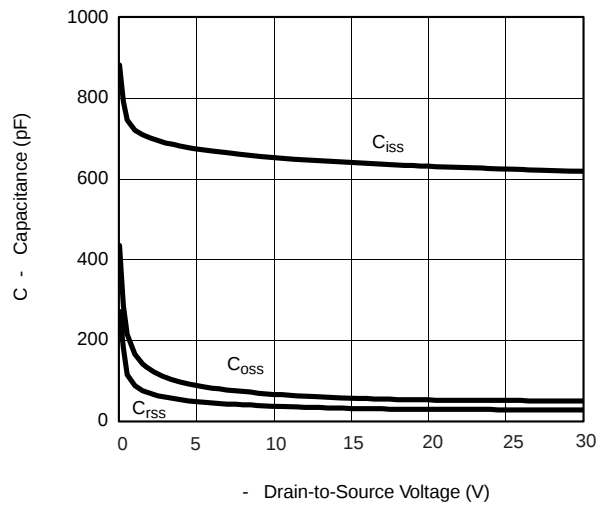
Output Characteristics



Transfer Characteristics



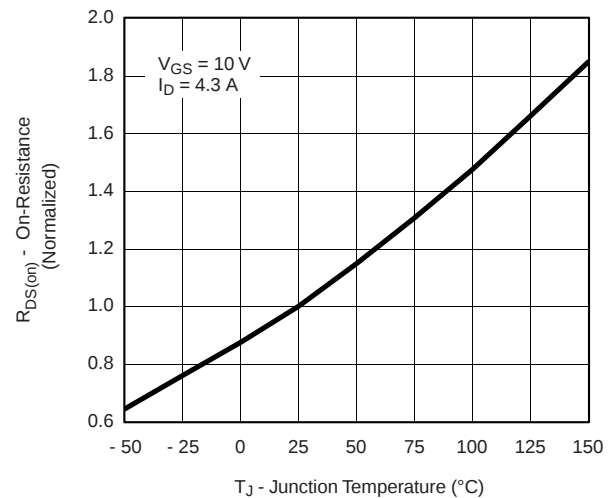
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



Gate Charge



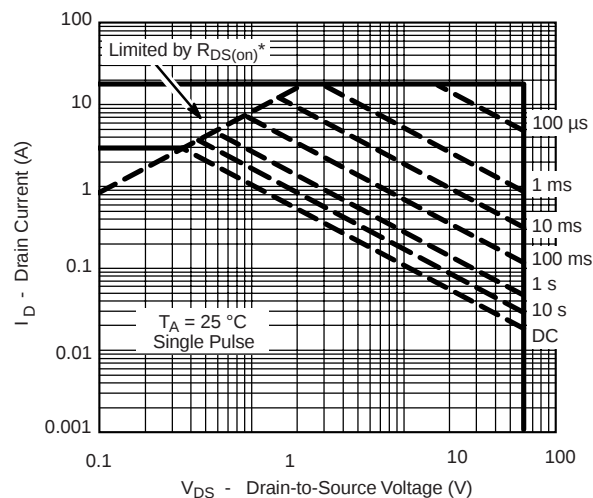
On-Resistance vs. Junction Temperature

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Source-Drain Diode Forward Voltage

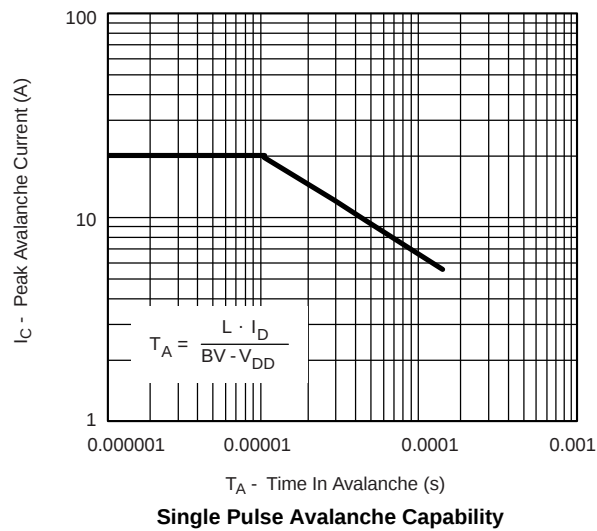
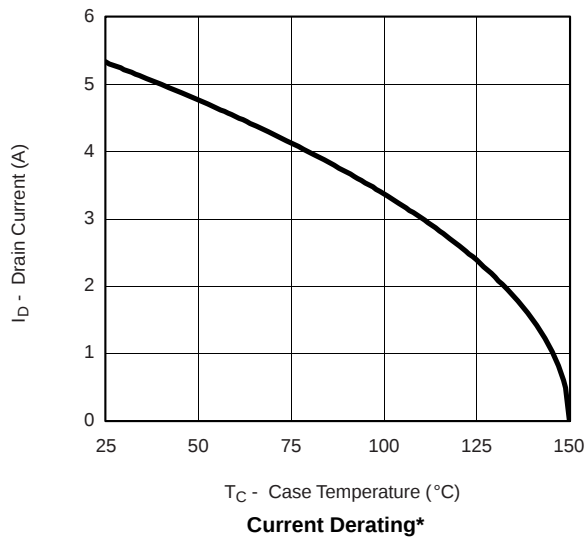
On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

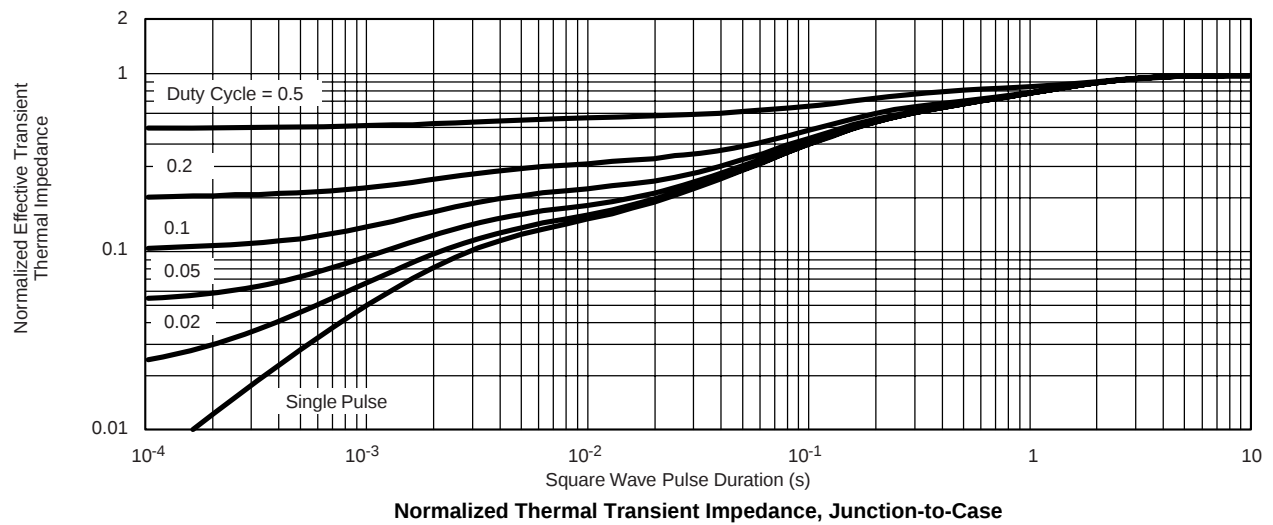
Single Pulse Power, Junction-to-Ambient


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

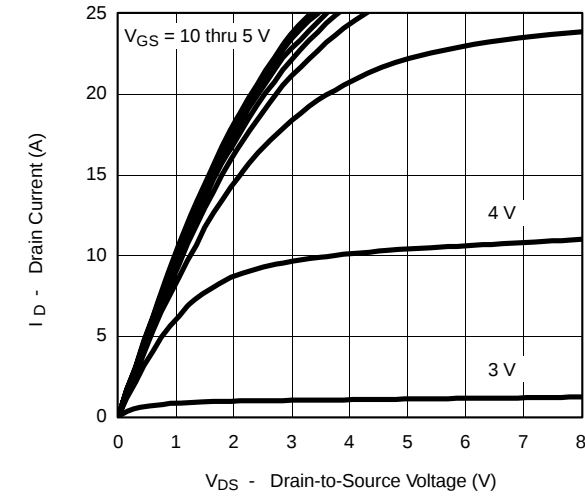
Safe Operating Area

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


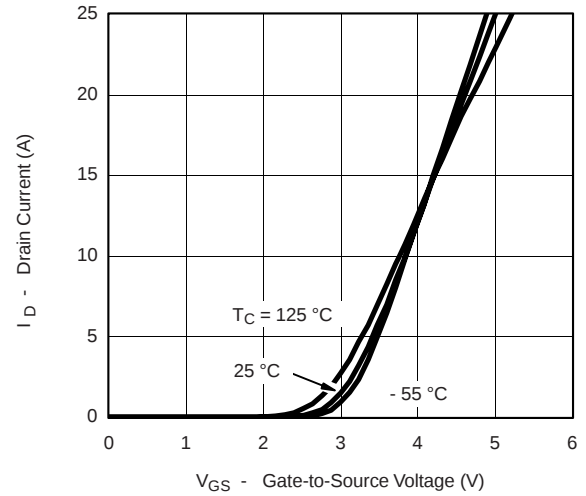
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


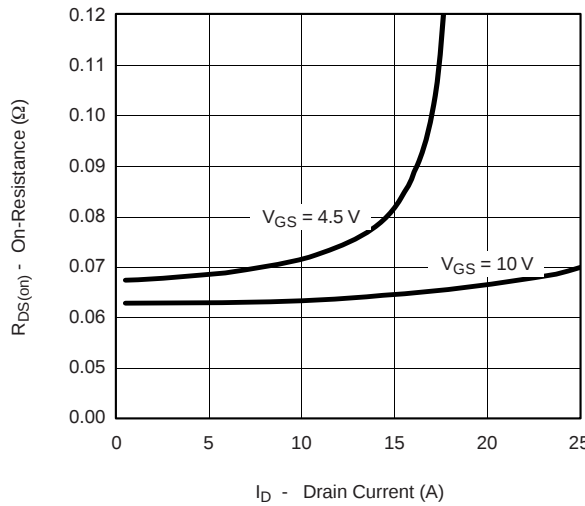
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



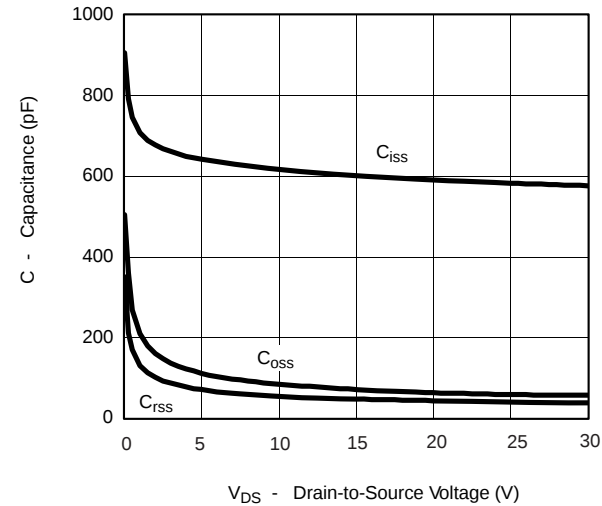
Output Characteristics



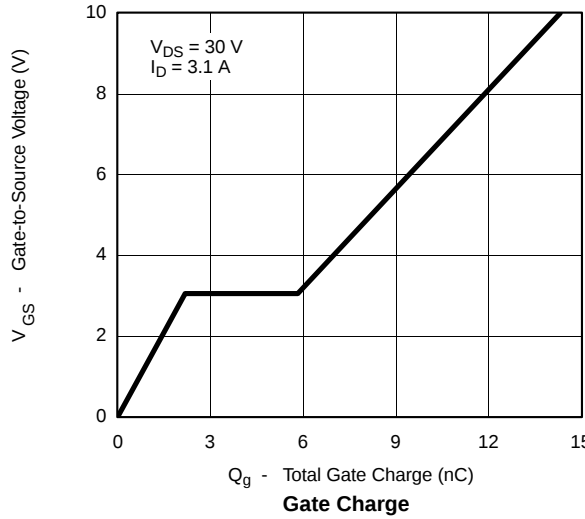
Transfer Characteristics



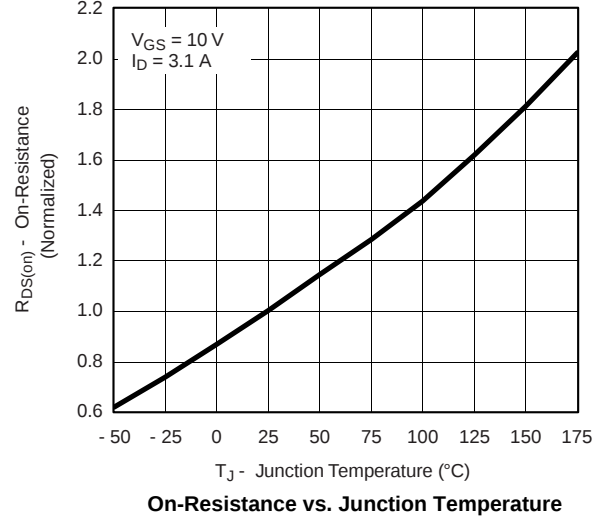
On-Resistance vs. Drain Current



Capacitance



Gate Charge



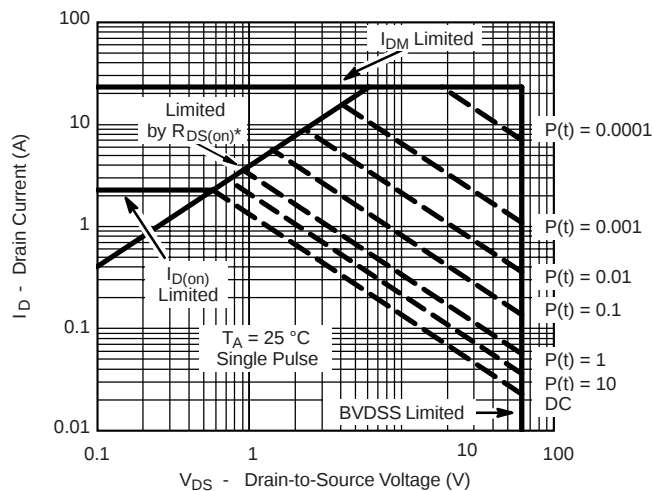
On-Resistance vs. Junction Temperature

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Source-Drain Diode Forward Voltage

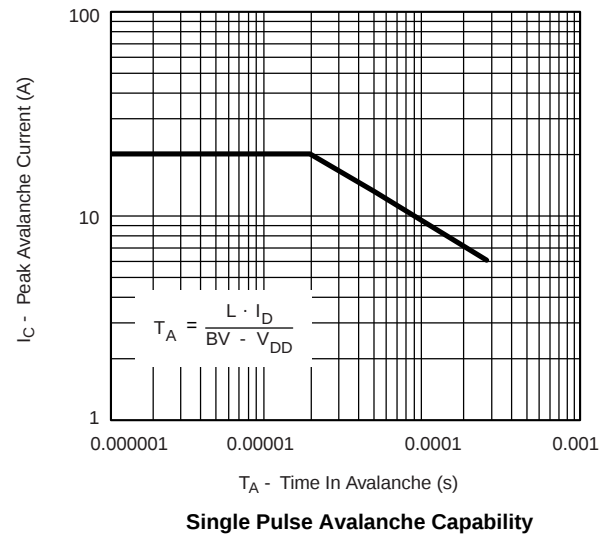
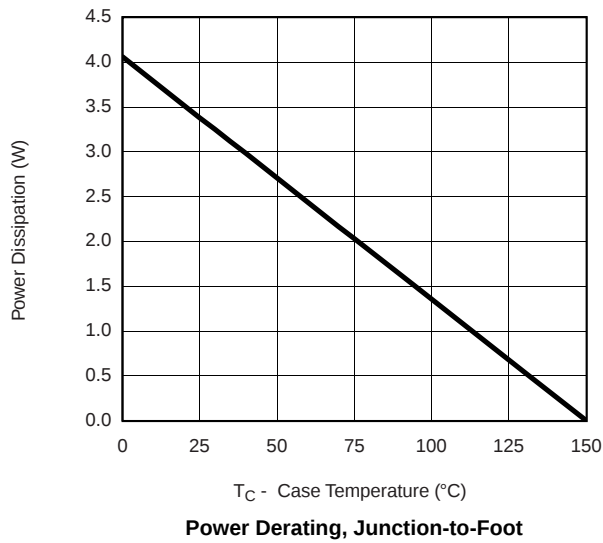
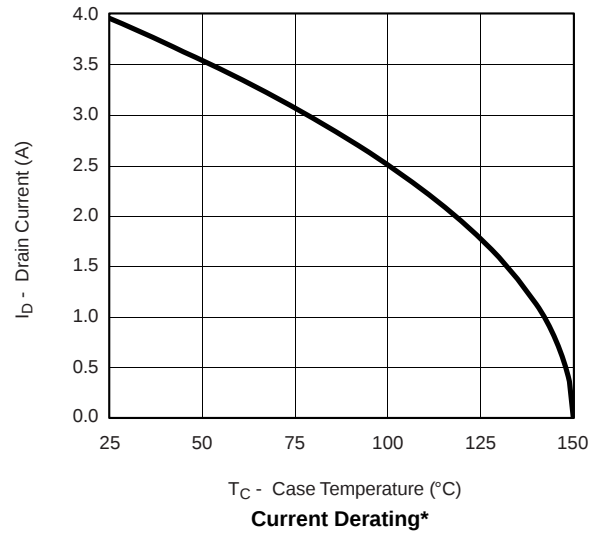
On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

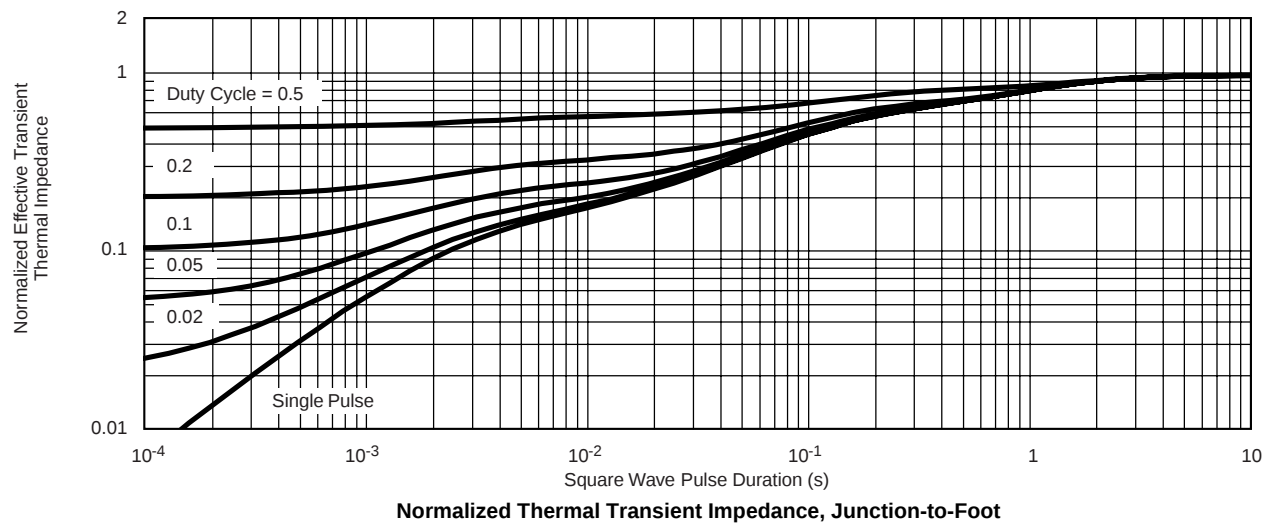
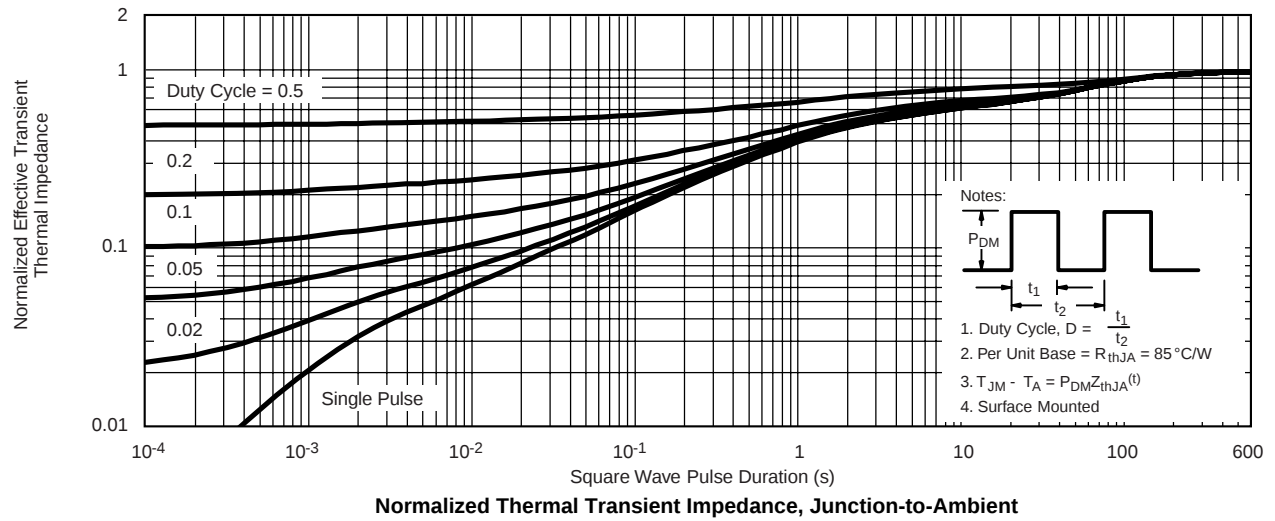
Single Pulse Power


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


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